

## NTE62 Silicon NPN Transistor High Voltage, Horizontal Deflection Output for TV

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	2500V
Collector–Emitter Voltage, $V_{CEO}$ .....	900V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	3A
Peak .....	7A
Collector Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	50W
Operating Junction Temperature, $T_j$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	–40° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 1000\text{V}, I_E = 0$	–	–	50	$\mu\text{A}$
		$V_{CB} = 2500\text{V}, I_E = 0$	–	–	1.0	mA
	$I_{CEO}$	$V_{CE} = 900\text{V}, I_B = 0$	–	–	10	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 6\text{V}, I_C = 0$	–	–	1.0	mA
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 1.5\text{A}$	3	–	15	–
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5\text{A}, I_B = 0.5\text{A}$	–	–	10	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1.5\text{A}, I_B = 0.5\text{A}$	–	–	1.25	V
Transition Frequency	$f_t$	$I_C = 1.5\text{A}$	–	–	1.0	$\mu\text{s}$

